

N-Channel Shielded Gate PowerTrench[®] MOSFET 100 V, 2.7 A, 109 m Ω

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 109 m Ω at V_{GS} = 10 V, I_D = 2.7 A
- Max $r_{DS(on)}$ = 176 m Ω at V_{GS} = 6 V, I_D = 2.1 A
- High performance trench technology for extremely low r_{DS(on)}
- High power and current handling capability in a widely used surface mount package
- Fast switching speed
- 100% UIL Tested
- RoHS Compliant

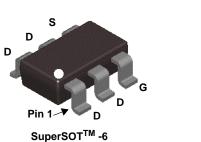


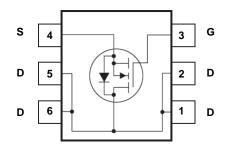
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that incorporates Shielded Gate technology. This process has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

Applications

- Load Switch
- Synchronous Rectifier
- Primary Switch





MOSFET Maximum Ratings $T_A = 25 \degree C$ unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DS}	Drain to Source Voltage		100	V	
V _{GS}	Gate to Source Voltage		±20	V	
I _D	Drain Current -Continuous	(Note 1a)	2.7		
	-Pulsed		12	— A	
E _{AS}	Single Pulse Avalanche Energy	(Note 3)	13	mJ	
P _D	Power Dissipation	(Note 1a)	1.6		
	Power Dissipation	(Note 1b)	0.8		
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C	

Thermal Characteristics

$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case		30	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	C/ VV

Package Marking and Ordering Information

Device Marking	Device	vice Package Reel Size		Tape Width	Quantity	
.861	FDC8601	SSOT-6	7 "	8 mm	3000 units	

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_{D} = 250 \ \mu A, V_{GS} = 0 \ V$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, referenced to 25 °C		70		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V			1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Chara	cteristics					
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \ \mu A$	2.0	3.0	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_{.1}}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, referenced to 25 °C		-8		mV/°C
J		V _{GS} = 10 V, I _D = 2.7 A		86	109	
r _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_D = 2.1 \text{ A}$		119	176	mΩ
		V _{GS} = 10 V, I _D = 2.7 A, T _J = 125 °C		144	183	
9 _{FS}	Forward Transconductance	V _{DD} = 10 V, I _D = 2.7 A		5		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance			155	210	pF
C _{oss}	Output Capacitance	── V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		46	65	pF
C _{rss}	Reverse Transfer Capacitance			2.2	5	pF
R _g	Gate Resistance			0.9		Ω
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time			4.5	10	ns
t _r	Rise Time	V _{DD} = 50 V, I _D = 2.7 A,		1.3	10	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		7.6	16	ns
t _f	Fall Time			2	10	ns
<u>_</u>	Total Gate Charge	V _{GS} = 0 V to 10 V		3	5	nC
Q _{g(TOT)}	Total Gate Charge	$V_{GS} = 0 V \text{ to } 5 V V_{DD} = 50 V$		1.7	3	nC
Q _{gs}	Total Gate Charge	I _D = 2.7 A		0.9		nC
Q _{gd}	Gate to Drain "Miller" Charge			0.8		nC
Drain-Soເ	Irce Diode Characteristics					
V _{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 2.7 A$ (Note 2)		0.85	1.3	V
t _{rr}	Reverse Recovery Time			34	54	ns
Q _{rr}	Reverse Recovery Charge	$I_F = 2.7 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		21	34	nC
IOTES: . R _{θJA} is the su	m of the junction-to-case and case-to-ambient thermal res ed by design while $R_{\theta CA}$ is determined by the user's board		as the solde	r mounting s	surface of the	e drain pin



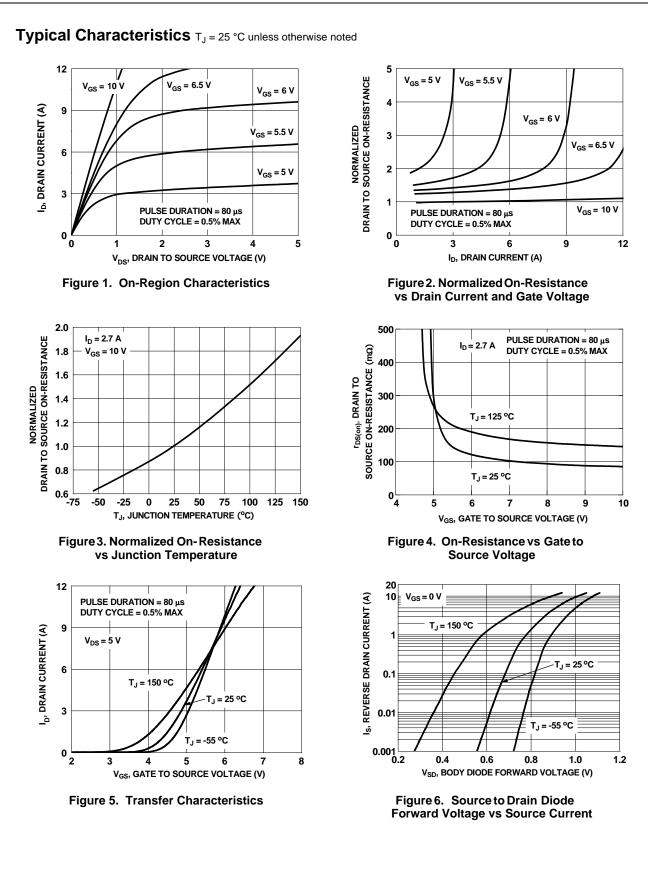
2. Pulse Test: Pulse Width < 300 $\mu s,$ Duty cycle < 2.0 %.

3. Starting T_J = 25 °C, L = 3 mH, I_{AS} = 3 A, V_{DD} = 100 V, V_{GS} = 10 V.

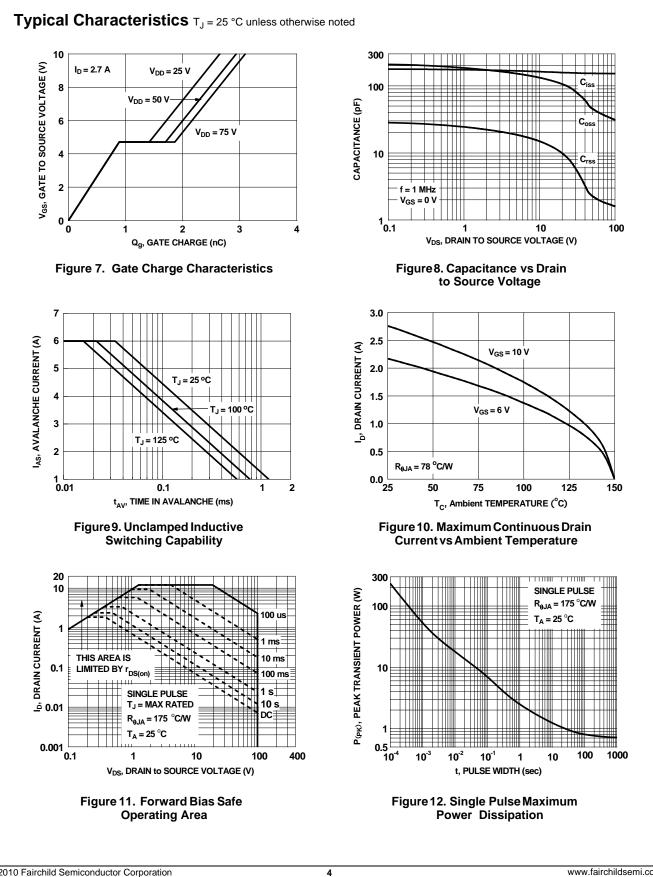
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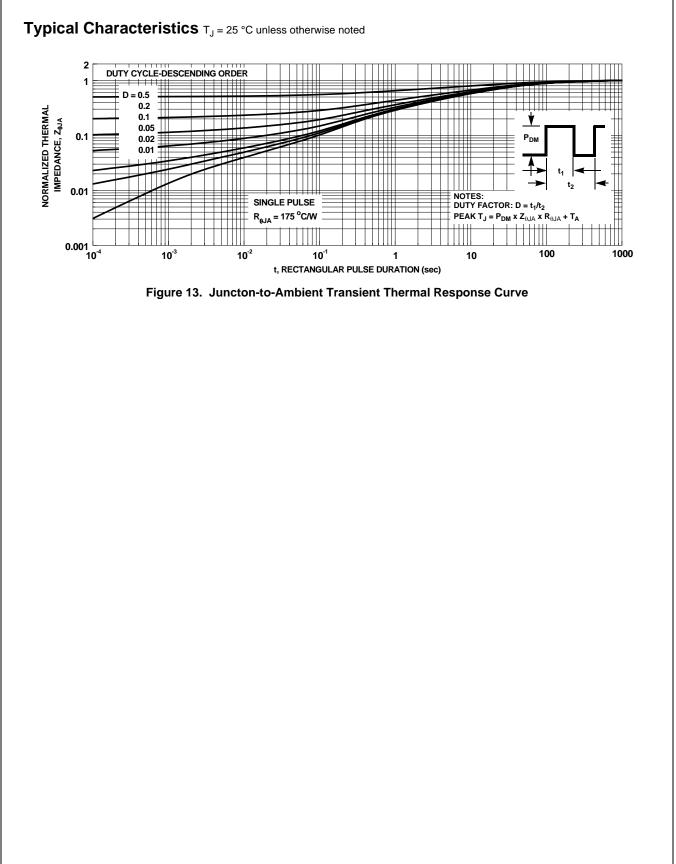
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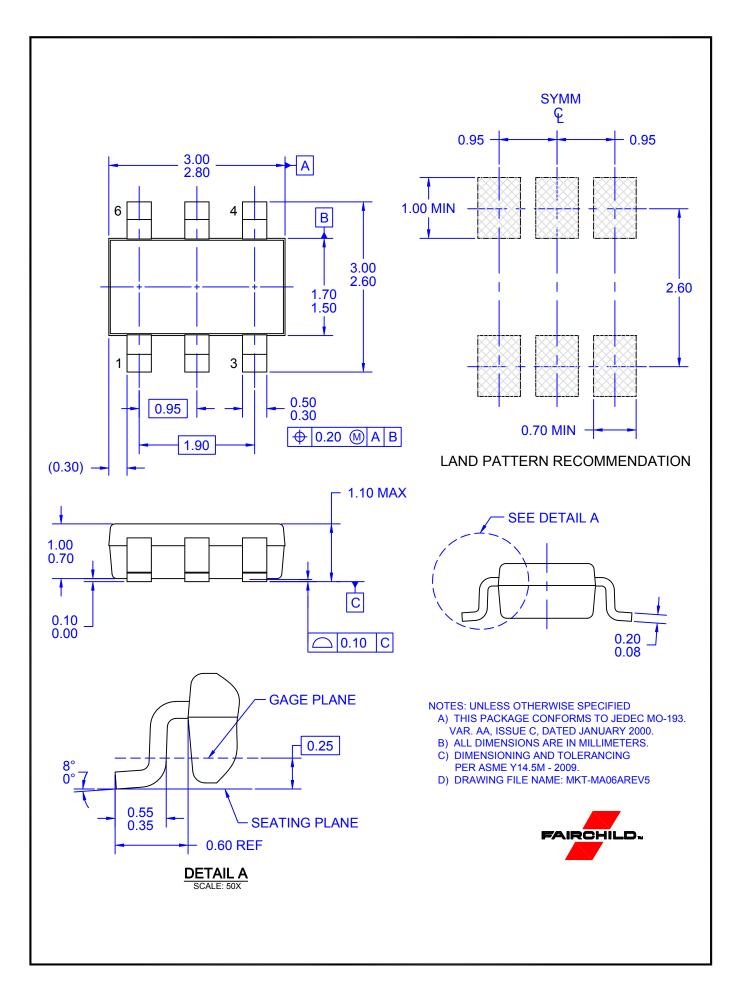


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